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– – of indium aluminum arsenide 256
– – of indium gallium aluminum phosphide 37
– – of indium gallium arsenide 256, 334, 1009
– – of indium gallium arsenide phosphide 37, 42 46
– – of zinc selenide 603
– by vapor phase epitaxy
– – through metalorganic chemical vapor deposition
– – – of indium gallium aluminum arsenide 600